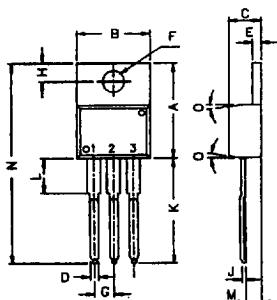
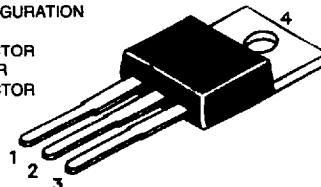


**TIP120, 121, 122      NPN PLASTIC POWER TRANSISTORS**  
**TIP125, 126, 127      PNP PLASTIC POWER TRANSISTORS**  
**Power Darlingtons for Linear and Switching Applications**

PIN CONFIGURATION  
 1. BASE  
 2. COLLECTOR  
 3. Emitter  
 4. COLLECTOR



DIM	MIN	MAX
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D	—	0.90
E	1.15	1.40
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J	—	0.56
K	12.70	14.73
L	—	6.35
M	2.03	2.92
N	—	31.24
O	7	DEG

#### ABSOLUTE MAXIMUM RATINGS

		120	121	122		
		125	126	127		
Collector-base voltage (open emitter)	V <sub>CBO</sub>	max.	60	80	100	V
Collector-emitter voltage (open base)	V <sub>CEO</sub>	max.	60	80	100	V
Collector current	I <sub>C</sub>	max.	5.0			A
Total power dissipation up to T <sub>C</sub> = 25°C	P <sub>tot</sub>	max.	65			W
Junction temperature	T <sub>j</sub>	max.	150			°C
Collector-emitter saturation voltage I <sub>C</sub> = 3 A; I <sub>B</sub> = 12 mA	V <sub>CEsat</sub>	max.	2.0			V
D.C. current gain I <sub>C</sub> = 0.5 A; V <sub>CE</sub> = 3 V	h <sub>FE</sub>	min.	1.0			K

#### RATINGS (at T<sub>A</sub>=25°C unless otherwise specified)

		120	121	122		
		125	126	127		
Collector-base voltage (open emitter)	V <sub>CBO</sub>	max.	60	80	100	V
Collector-emitter voltage (open base)	V <sub>CEO</sub>	max.	.60	80	100	V
Emitter-base voltage (open collector)	V <sub>EBO</sub>	max.	5.0			V

Collector current	$I_C$	max.	5.0	A
Collector current (peak)	$I_{CM}$	max.	8	A
Base current	$I_B$	max.	120	mA
Total power dissipation up to $T_C = 25^\circ\text{C}$	$P_{tot}$	max.	65	W
Derate above $25^\circ\text{C}$		max	0.52	$\text{W}/^\circ\text{C}$
Total power dissipation up to $T_A = 25^\circ\text{C}$	$P_{tot}$	max.	2	W
Derate above $25^\circ\text{C}$		max	0.016	$\text{W}/^\circ\text{C}$
Junction temperature	$T_j$	max.	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$		-65 to +150	$^\circ\text{C}$

**THERMAL RESISTANCE**

From junction to ambient	$R_{th j-a}$	62.5	$^\circ\text{C}/\text{W}$
From junction to case	$R_{th j-c}$	1.92	$^\circ\text{C}/\text{W}$

**CHARACTERISTICS**

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified		120	121	122
		125	126	127

Collector cutoff current					
$I_E = 0; V_{CB} = 60 \text{ V}$	$I_{CBO}$	max.	0.2	-	- mA
$I_E = 0; V_{CB} = 80 \text{ V}$	$I_{CBO}$	max.	-	0.2	- mA
$I_E = 0; V_{CB} = 100 \text{ V}$	$I_{CBO}$	max.	-	-	0.2 mA
$I_B = 0; V_{CE} = 30 \text{ V}$	$I_{CEO}$	max.	0.5	-	- mA
$I_B = 0; V_{CE} = 40 \text{ V}$	$I_{CEO}$	max.	-	0.5	- mA
$I_B = 0; V_{CE} = 50 \text{ V}$	$I_{CEO}$	max.	-	-	0.5 mA
Emitter cut-off current					
$I_C = 0; V_{EB} = 5 \text{ V}$	$I_{EBO}$	max.	2.0		mA
Breakdown voltages					
$I_C = 100 \text{ mA}; I_B = 0$	$V_{CEO(sus)}^*$	min.	60	80	100 V
$I_C = 1 \text{ mA}; I_E = 0$	$V_{CBO}$	min.	60	80	100 V
$I_E = 1 \text{ mA}; I_C = 0$	$V_{EBO}$	min.	5.0		V
Saturation voltages					
$I_C = 3.0 \text{ A}; I_B = 12 \text{ mA}$	$V_{CEsat}^*$	max.	2.0		V
$I_C = 5.0 \text{ A}; I_B = 20 \text{ mA}$	$V_{CEsat}^*$	max.	4.0		V
Base-emitter on voltage					
$I_C = 3 \text{ A}; V_{CE} = 3 \text{ V}$	$V_{BE(on)}^*$	max.	2.5		V
D.C. current gain					
$I_C = 0.5 \text{ A}; V_{CE} = 3 \text{ V}$	$h_{FE}^*$	min.	1.0		K
$I_C = 3 \text{ A}; V_{CE} = 3 \text{ V}$		min.	1.0		K
Small signal current gain					
$I_C = 3 \text{ A}; V_{CE} = 4 \text{ V}; f = 1 \text{ MHz}$	$ h_{fe} $	min.	4.0		
Output capacitance at $f = 0.1 \text{ MHz}$					
$I_E = 0; V_{CB} = 10 \text{ V}$	PNP	$C_o$	max.	300	pF
	NPN	$C_o$	max.	200	pF

\* Pulse test: pulse width  $\leq 300 \mu\text{s}$ ; duty cycle  $\leq 2\%$ .